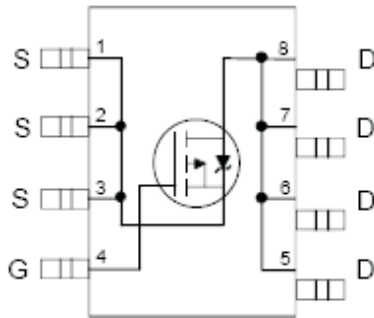
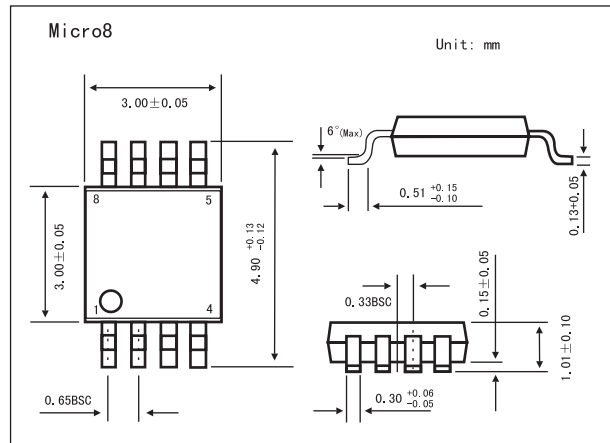


HEXFET[®] Power MOSFET

KRF7606

■ Features

- Generation V Technology
- Ultra Low On-Resistance
- P-Channel MOSFET
- Very Small SOIC Package
- Low Profile (<1.1mm)
- Available in Tape & Reel
- Fast Switching



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Continuous Drain Current, $V_{GS} @ -10V @ T_a = 25^\circ\text{C}$	I_D	-3.6	A
Continuous Drain Current, $V_{GS} @ -10V @ T_a = 70^\circ\text{C}$	I_D	-2.9	
Pulsed Drain Current *1	I_{DM}	-29	
Power Dissipation @ $T_a = 25^\circ\text{C}$	P_D	1.8	W
Power Dissipation @ $T_a = 70^\circ\text{C}$		1.1	
Linear Derating Factor		14	
Gate-to-Source Voltage	V_{GS}	± 20	V
Gate-to-Source Voltage Single Pulse $t_p < 10 \mu\text{s}$	V_{GSM}	30	V
Peak Diode Recovery dv/dt *2	dv/dt	-5.0	V/ns
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to + 150	$^\circ\text{C}$
Maximum Junction-to-Ambient *3	$R_{\theta JA}$	70	$^\circ\text{C/W}$


*1 Repetitive rating; pulse width limited by max. junction temperature.

*2 $I_{SD} \leq -2.4\text{A}$, $di/dt \leq -130\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$

*3 Surface mounted on FR-4 board, $t \leq 10\text{sec}$.

KRF7606

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250 \mu A$	-30			V
Breakdown Voltage Temp. Coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	$I_D = -1mA, \text{Reference to } 25^\circ C$		-0.024		V/°C
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -2.4A^{*1}$		0.075	0.09	mΩ
		$V_{GS} = -4.5V, I_D = -1.2A^{*1}$		0.130	0.15	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-1.0			V
Forward Transconductance	g_{fs}	$V_{DS} = -10V, I_D = -1.2A^{*1}$	2.3			S
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS} = -24V, V_{GS} = 0V$			-1.0	μA
		$V_{DS} = -24V, V_{GS} = 0V, T_J = 125^\circ C$			-25	
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS} = -20V$			-100	nA
Gate-to-Source Reverse Leakage		$V_{GS} = 20V$			100	
Total Gate Charge	Q_g	$I_D = -2.4A$		20	30	nC
Gate-to-Source Charge	Q_{gs}	$V_{DS} = -24V$		2.1	3.1	
Gate-to-Drain ("Miller") Charge	Q_{gd}	$V_{GS} = -10V$		7.6	11	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10V$		13		ns
Rise Time	t_r	$I_D = -2.4A$		20		
Turn-Off Delay Time	$t_{d(off)}$	$R_G = 6 \Omega$		43		
Fall Time	t_f	$R_D = 4.0 \Omega$		39		
Input Capacitance	C_{iss}	$V_{GS} = 0V$		520		pF
Output Capacitance	C_{oss}	$V_{DS} = -25V$		300		
Reverse Transfer Capacitance	C_{rss}	$f = 1.0MHz$		140		
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode. 			-1.8	A
Pulsed Source Current (Body Diode) *2	I_{SM}				-29	
Diode Forward Voltage	V_{SD}	$T_J = 25^\circ C, I_S = -2.4A, V_{GS} = 0V^{*1}$			-1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ C, I_F = -2.4A$		43	64	ns
Reverse Recovery Charge	Q_{rr}	$di/dt = -100A/\mu s^{*1}$		50	76	μC

*1 Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.

*2 Repetitive rating; pulse width limited by max. junction temperature.